

SANYO

No.3708

2SC4675

NPN Epitaxial Planar Silicon Transistor

High-Current Switching Applications

Features

- Adoption of MBIT process.
- Low saturation voltage.
- Fast switching speed.
- Large current capacity.

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

			unit
Collector-to-Base Voltage	V_{CB0}	30	V
Collector-to-Emitter Voltage	V_{CE0}	20	V
Emitter-to-Base Voltage	V_{EB0}	5	V
Collector Current	I_C	8	A
Peak Collector Current	i_{cp}	12	A
Base Current	I_B	1.5	A
Collector Dissipation	P_C	1.5	W

 $T_c = 25^\circ\text{C}$

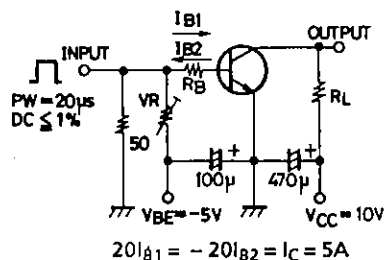
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics at $T_a = 25^\circ\text{C}$

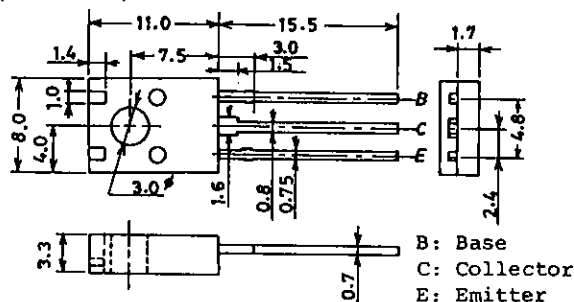
			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 20\text{V}, I_E = 0$			1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 4\text{V}, I_C = 0$			1	μA
DC Current Gain	$h_{FE}(1)$	$V_{CE} = 2\text{V}, I_C = 500\text{mA}$	100*		400*	
	$h_{FE}(2)$	$V_{CE} = 2\text{V}, I_C = 6\text{A}$	70			
Gain-Bandwidth Product	f_T	$V_{CE} = 2\text{V}, I_C = 500\text{mA}$		250		MHz
Output Capacitance	c_{ob}	$V_{CB} = 10\text{V}, f = 1\text{MHz}$		60		pF
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = 5\text{A}, I_B = 250\text{mA}$		220	400	mV
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = 5\text{A}, I_B = 250\text{mA}$		1	1.3	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 10\mu\text{A}, I_E = 0$	30			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1\text{mA}, R_{BE} = \infty$	20			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 10\mu\text{A}, I_C = 0$	5			V
Turn-ON Time	t_{on}	See specified Test Circuit.		30		ns
Storage Time	t_{stg}	"		250		ns
Fall Time	t_f	"		15		ns

* : The 2SC4675 is classified by 500mA h_{FE} as follows.

100	R	200	140	S	280	200	T	400
-----	---	-----	-----	---	-----	-----	---	-----

Switching Time Test Circuit**Package Dimensions 2042A**

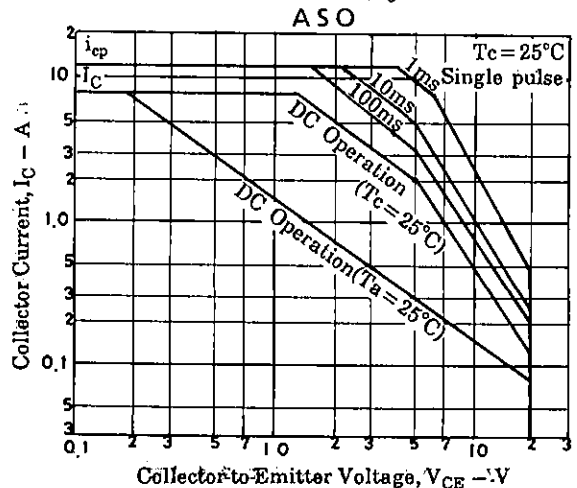
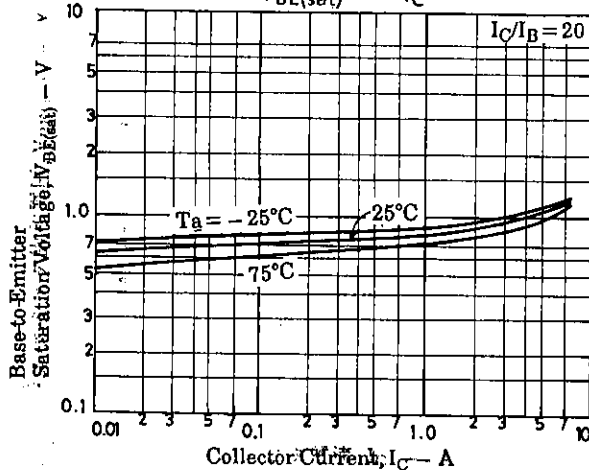
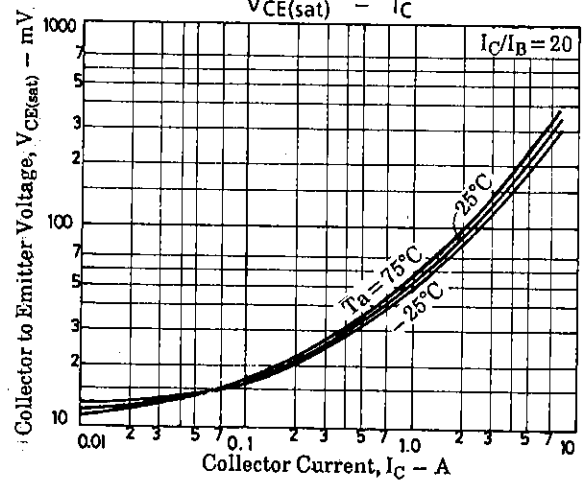
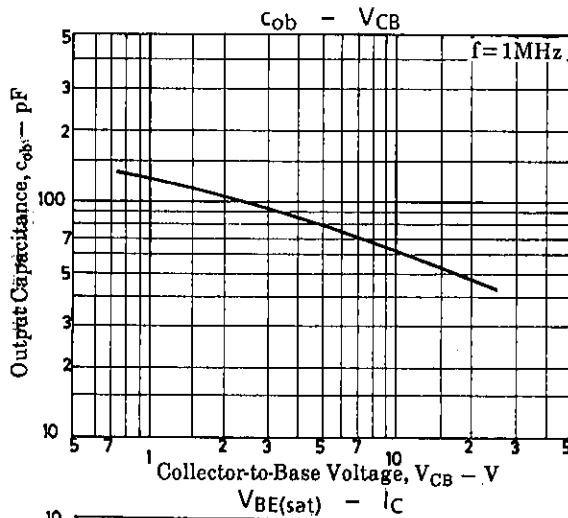
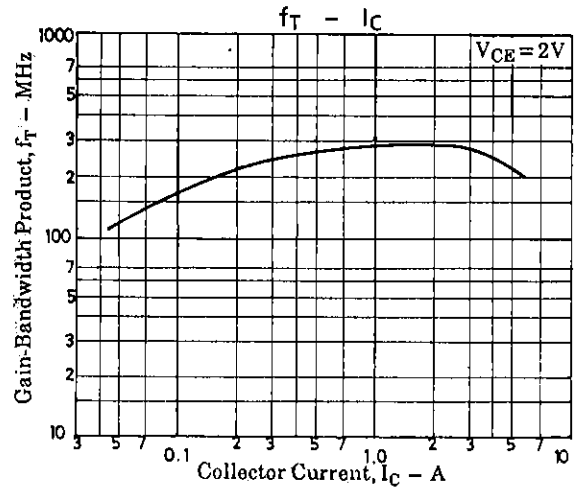
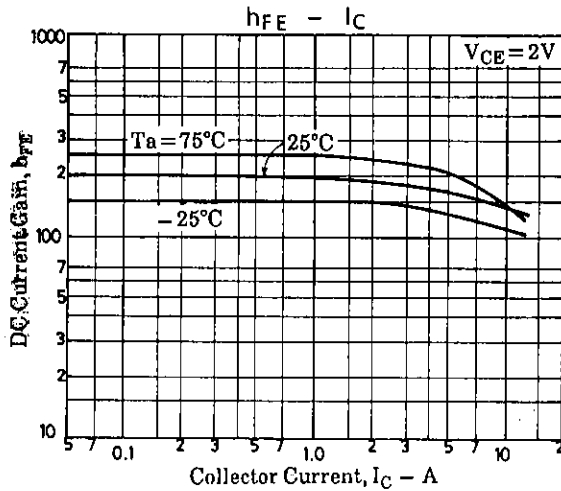
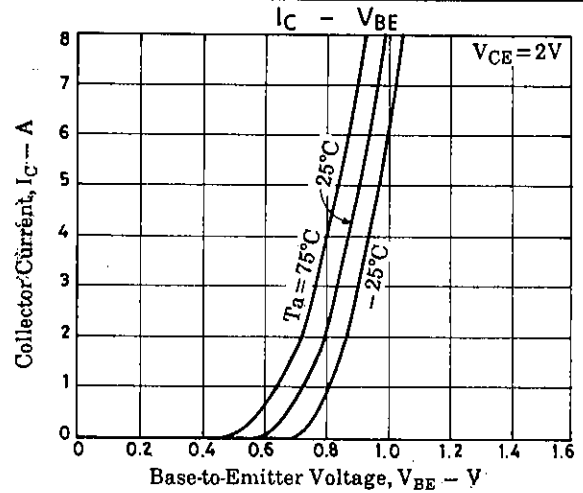
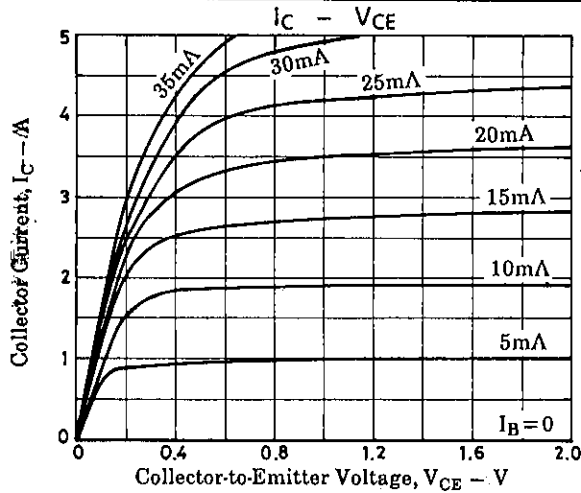
(unit : mm)

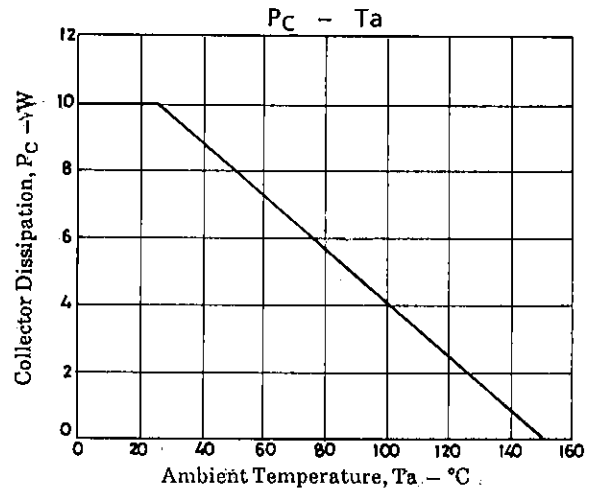
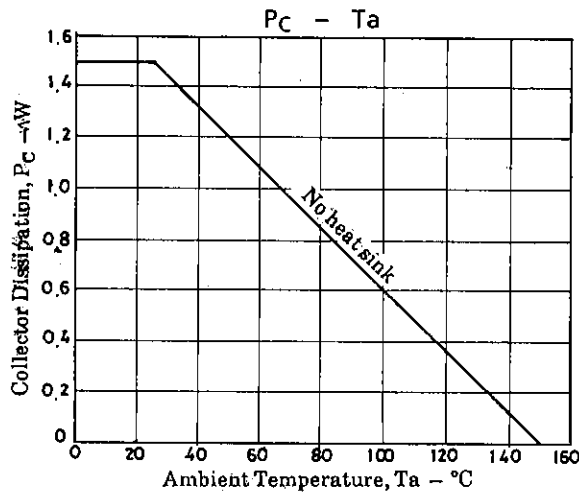


SANYO: T0126ML

SANYO Electric Co., Ltd. Semiconductor Business Headquarters
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN

5201MH, KOTO No.3708-1/3





- No products described or contained herein are intended for use in surgical implants, life-support systems, aerospace equipment, nuclear power control systems, vehicles, disaster/crime-prevention equipment and the like, the failure of which may directly or indirectly cause injury, death or property loss.
- Anyone purchasing any products described or contained herein for an above-mentioned use shall:
 - ① Accept full responsibility and indemnify and defend SANYO ELECTRIC CO., LTD., its affiliates, subsidiaries and distributors and all their officers and employees, jointly and severally, against any and all claims and litigation and all damages, cost and expenses associated with such use.
 - ② Not impose any responsibility for any fault or negligence which may be cited in any such claim or litigation on SANYO ELECTRIC CO., LTD., its affiliates, subsidiaries and distributors or any of their officers and employees jointly or severally.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. SANYO believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.